

# YJ Planar Schottky Barrier Diode Die Specification

200V 30A, 122mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB122H200AS-290A

## Main Products Characteristics

- Average forward current:  $I_F(AV) = 30 \text{ A}$
- Maximum operating junction temperature:  $T_j = 175 \text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

## Maximum Ratings

## Static Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

$I_F = 15\text{A}$

Pulse Test:  $t_p = 300 \mu\text{s}$ , 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die SizC.33 10.68 -20\*